

UTT50P10

Preliminary

TO-220

-50A, -100V P-CHANNEL POWER MOSFET

DESCRIPTION

The UTC **UTT50P10** is a P-channel power MOSFET using UTC's advanced technology to provide the customers with high switching speed and a minimum on-state resistance. It can also withstand high energy in the avalanche.

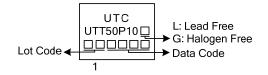
FEATURES

- * V_{DS}= -100V
- * I_D = -50A
- * $R_{DS(ON)}$ < 60m Ω @ V_{GS} = -10V, I_D = -20A
- * High Switching Speed

ORDERING INFORMATION

Ordering Number			Deekege	Pin Assignment			Decking		
Lead Free	Halogen Free		Package	1	2	3	Packing		
UTT50P10L-TA3-T	UTT50P10G-TA3-T		TO-220	G	D	S	Tube		
Note: Pin Assignment: G: Gate D: Drain S: Source									
UTT50P10L-TA3-T (1)Packing Type (2)Package Type			(1) T: Tube (2) TA3: TO-220						
(3)Green Package			(3) L: Lead Free, G: Halogen Free and Lead Free						

MARKING



ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Gate-Source Voltage		V _{GSS}	±20	V	
Drain Current	Continuous	I _D	-50	А	
	Pulsed	I _{DM}	-90	А	
Power Dissipation		PD	225	W	
Junction Temperature		ТJ	+150	°C	
Storage Temperature		T _{STG}	-55~+150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Case	θ _{JC}	0.55	°C/W

ELECTRICAL CHARACTERISTICS

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =-250μA, V _{GS} =0V	-100			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =0.8×Max.rating, V _{GS} =0V, T _J =25°C		-1		
			V _{DS} =0.8×Max.rating, V _{GS} =0V, T _J =125°C			-500	μA
Gate- Source Leakage	Forward		V _{GS} =+20V			+100	nA
Current	Reverse	I _{GSS}	V _{GS} =-20V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =-250µA	-1		-3	V
Static Drain-Source On-State Resistance		Resident	V _{GS} =-10V, I _D =-20A			60	mΩ
			V _{GS} =-4.5V, I _D =-15A			65	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		CISS	V _{GS} =0V, V _{DS} =-50V, f=1.0MHz		4200		pF
Output Capacitance		Coss			250		pF
Reverse Transfer Capacitance		C _{RSS}			110		pF
SWITCHING PARAMETER	S						
Turn-ON Delay Time		t _{D(ON)}			80	130	ns
Rise Time		t _R	V _{DD} =-50V, V _{GS} =-10V, I _D =-50A, R _G =1Ω		76	130	ns
Turn-OFF Delay Time		t _{D(OFF)}	v_{DD} =-50V, v_{GS} =-10V, I_D =-50A, R_G =12		740	900	ns
Fall-Time		t _F			200	400	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Drain Source Diede Ferward Valtere	V_{SD}	I _F =-20A, V _{GS} =0V, Pulse test, t≤300µs,	-1.0	10	-1.5	V	
Drain-Source Diode Forward Voltag		duty cycle d≤2%		-1.0			
Body Diode Reverse Recovery Time		t	T _J =25°C, I _F =-20A, V _R =-50V,		80	120	ns
Body Diode Neverse Recor		t _{RR}	di/dt=-100A/µs		00	120	115

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